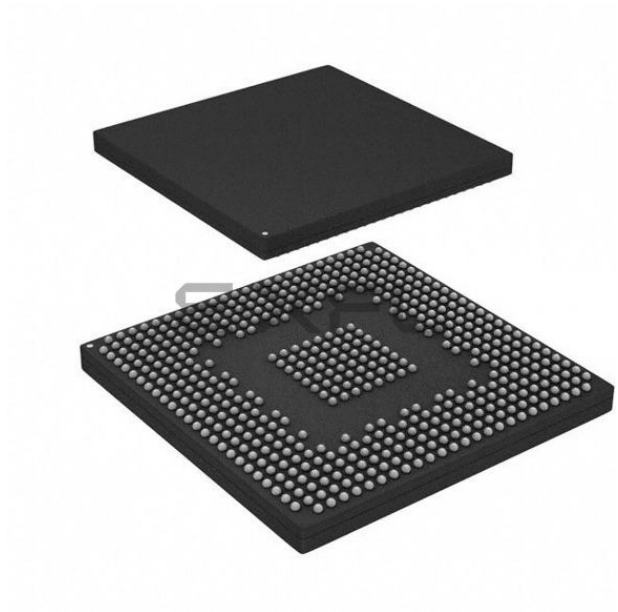

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z7
Core Size	32-Bit Tri-Core
Speed	264MHz
Connectivity	CANbus, EBI/EMI, Ethernet, FlexCANbus, LINbus, SCI, SPI
Peripherals	DMA, LVD, POR, Zipwire
Number of I/O	-
Program Memory Size	8MB (8M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 16b Sigma-Delta, eQADC
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	516-BGA
Supplier Device Package	516-MAPBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5777cdk3mmo3r

Table of Contents

- Enhanced Modular Input/Output System (eMIOS) supporting 32 unified channels with each channel capable of single action, double action, pulse width modulation (PWM) and modulus counter operation
- Two Enhanced Queued Analog-to-Digital Converter (eQADC) modules with:
  - Two separate analog converters per eQADC module
  - Support for a total of 70 analog input pins, expandable to 182 inputs with off-chip multiplexers
  - Interface to twelve hardware Decimation Filters
  - Enhanced "Tap" command to route any conversion to two separate Decimation Filters
- Four independent 16-bit Sigma-Delta ADCs (SDADCs)
- 10-channel Reaction Module
- Ethernet (FEC)
- Two PSI5 modules
- Two SENT Receiver (SRX) modules supporting 12 channels
- Zipwire: SIPI and LFAST modules
- Five Deserial Serial Peripheral Interface (DSPI) modules
- Five Enhanced Serial Communication Interface (eSCI) modules
- Four Controller Area Network (FlexCAN) modules
- Two M_CAN modules that support FD
- Fault Collection and Control Unit (FCCU)
- Clock Monitor Units (CMUs)
- Tamper Detection Module (TDM)
- Cryptographic Services Engine (CSE)
  - Complies with *Secure Hardware Extension (SHE) Functional Specification Version 1.1* security functions
  - Includes software selectable enhancement to key usage flag for MAC verification and increase in number of memory slots for security keys
- PASS module to support security features
- Nexus development interface (NDI) per IEEE-ISTO 5001-2003 standard, with some support for 2010 standard
- Device and board test support per Joint Test Action Group (JTAG) IEEE 1149.1 and 1149.7
- On-chip voltage regulator controller (VRC) that derives the core logic supply voltage from the high-voltage supply
- On-chip voltage regulator for flash memory
- Self Test capability

Table 1. Absolute maximum ratings (continued)

Symbol	Parameter	Conditions[1]	Value		Unit
			Min	Max	
MSL	Moisture sensitivity level[11]	—	—	3	—

1. Voltages are referred to V_{SS} if not specified otherwise
2. Allowed 1.45 V – 1.5 V for 60 seconds cumulative time at maximum T_J = 150 °C; remaining time as defined in note 3 and note 4
3. Allowed 1.375 V – 1.45 V for 10 hours cumulative time at maximum T_J = 150 °C; remaining time as defined in note 4
4. 1.32 V – 1.375 V range allowed periodically for supply with sinusoidal shape and average supply value below 1.275 V at maximum T_J = 150 °C
5. Allowed 5.5 V – 6.0 V for 60 seconds cumulative time with no restrictions, for 10 hours cumulative time device in reset, T_J = 150 °C; remaining time at or below 5.5 V
6. Allowed 3.6 V – 4.5 V for 60 seconds cumulative time with no restrictions, for 10 hours cumulative time device in reset, T_J = 150 °C; remaining time at or below 3.6 V
7. The maximum input voltage on an I/O pin tracks with the associated I/P supply maximum. For the injection current condition on a pin, the voltage will be equal to the supply plus the voltage drop across the internal ESD diode from I/O pin to supply. The diode voltage varies greatly across process and temperature, but a value of 0.3V can be used for nominal calculations.
8. The sum of all controller pins (including both digital and analog) must not exceed 200 mA. A V_{DDEx}/V_{DDEHx} power segment is defined as one or more GPIO pins located between two V_{DDEx}/V_{DDEHx} supply pins.
9. The average current values given in I/O pad current specifications should be used to calculate total I/O segment current.
10. Solder profile per IPC/JEDEC J-STD-020D
11. Moisture sensitivity per JEDEC test method A112

3.2 Electromagnetic interference (EMI) characteristics

Test reports with EMC measurements to IC-level IEC standards are available on request.

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions, go to nxp.com and perform a keyword search for "radiated emissions."

3.3 Electrostatic discharge (ESD) characteristics

Table 2. ESD Ratings[1, 2]

Symbol	Parameter	Conditions	Value	Unit
V_{HBM}	ESD for Human Body Model (HBM)	All pins	2000	V
V_{CDM}	ESD for Charged Device Model (CDM)	Corner pins	750	V
		Non-corner pins	500	

1. All ESD testing is in conformity with CDF-AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits.
2. A device will be defined as a failure if after exposure to ESD pulses the device no longer meets the device specification requirements.

13. For supply voltages between 3.0 V and 4.0 V there will be no guaranteed precision of ADC (accuracy/linearity). ADC will recover to a fully functional state when the voltage rises above 4.0 V.
14. Full device lifetime without performance degradation
15. I/O and analog input specifications are only valid if the injection current on adjacent pins is within these limits. See the absolute maximum ratings table for maximum input current for reliability requirements.
16. The I/O pins on the device are clamped to the I/O supply rails for ESD protection. When the voltage of the input pin is above the supply rail, current will be injected through the clamp diode to the supply rail. For external RC network calculation, assume a typical 0.3 V drop across the active diode. The diode voltage drop varies with temperature.
17. The sum of all controller pins (including both digital and analog) must not exceed 200 mA. A V_{DDEx}/V_{DDEHx} power segment is defined as one or more GPIO pins located between two V_{DDEx}/V_{DDEHx} supply pins.
18. The average current values given in I/O pad current specifications should be used to calculate total I/O segment current.

3.5 DC electrical specifications

NOTE

I_{DDA_MISC} is the sum of current consumption of IRC, I_{TRNG}, and I_{STBY} in the 5 V domain. IRC current is provided in the IRC specifications.

NOTE

I/O, XOSC, EQADC, SDADC, and Temperature Sensor current specifications are in those components' dedicated sections.

Table 4. DC electrical specifications

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
I_{DD}	Operating current on the V_{DD} core logic supply[1]	LVD/HVD enabled, V_{DD} = 1.2 V to 1.32 V	—	0.65	1.35	A
		LVD/HVD disabled, V_{DD} = 1.2 V to 1.38 V	—	0.65	1.4	
I_{DD_PE}	Operating current on the V_{DD} supply for flash memory program/erase	—	—	—	85	mA
I_{DDPMC}	Operating current on the V_{DDPMC} supply[2]	Flash memory read	—	—	40	mA
		Flash memory program/erase	—	—	70	
		PMC only	—	—	35	
	Operating current on the V_{DDPMC} supply (internal core regulator bypassed)	Flash memory read	—	—	10	mA
		Flash memory program/erase	—	—	40	
		PMC only	—	—	5	
I_{REGCTL}	Core regulator DC current output on V_{REGCTL} pin	—	—	—	25	mA
I_{STBY}	Standby RAM supply current (T_J = 150°C)	1.08 V	—	—	1140	µA
		1.25 V to 5.5 V	—	—	1170	
I_{DD_PWR}	Operating current on the V_{DDPWR} supply	—	—	—	50	mA
I_{BG_REF}	Bandgap reference current consumption[3]		—	—	600	µA
I_{TRNG}	True Random Number Generator current	—	—	—	2.1	mA

1. PCR[DSC] values refer to the setting of that register field in the SIU.

3.6.3 I/O pad current specifications

The I/O pads are distributed across the I/O supply segments. Each I/O supply segment is associated with a V_{DDEx} supply segment.

Table 11 provides I/O consumption figures.

To ensure device reliability, the average current of the I/O on a single segment should remain below the I_{MAXSEG} value given in Table 1.

To ensure device functionality, the average current of the I/O on a single segment should remain below the I_{MAXSEG} value given in Table 3.

NOTE

The MPC5777C I/O Signal Description and Input Multiplexing Tables are contained in a Microsoft Excel® file attached to the Reference Manual. In the spreadsheet, select the I/O Signal Table tab.

Table 11. I/O consumption

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
I_{AVG_GPIO}	Average I/O current for GPIO pads (per pad)	C_L = 25 pF, 2 MHz V_{DDEx} = 5.0 V ± 10%	—	—	0.42	mA
		C_L = 50 pF, 1 MHz V_{DDEx} = 5.0 V ± 10%	—	—	0.35	
I_{AVG_EBI}	Average I/O current for external bus output pins (per pad)	C_{DRV} = 10 pF, f_{EBI} = 66 MHz V_{DDEx} = 3.3 V ± 10%	—	—	9	mA
		C_{DRV} = 20 pF, f_{EBI} = 66 MHz V_{DDEx} = 3.3 V ± 10%	—	—	18	
		C_{DRV} = 30 pF, f_{EBI} = 66 MHz V_{DDEx} = 3.3 V ± 10%	—	—	30	

3.7 Oscillator and PLL electrical specifications

The on-chip dual PLL—consisting of the peripheral clock and reference PLL (PLL0) and the frequency-modulated system PLL (PLL1)—generates the system and auxiliary clocks from the main oscillator driver.

Table 18. SDADC electrical specifications (continued)

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
$SNR_{DIFF150}$	Signal to noise ratio in differential mode, 150 Ksps output rate	4.5 V < V_{DDA_SD} < 5.5 V[8, 9] V_{RH_SD} = V_{DDA_SD} GAIN = 1	80	—	—	dB
		4.5 V < V_{DDA_SD} < 5.5 V[8, 9] V_{RH_SD} = V_{DDA_SD} GAIN = 2	77	—	—	
		4.5 V < V_{DDA_SD} < 5.5 V[8, 9] V_{RH_SD} = V_{DDA_SD} GAIN = 4	74	—	—	
		4.5 V < V_{DDA_SD} < 5.5 V[8, 9] V_{RH_SD} = V_{DDA_SD} GAIN = 8	71	—	—	
		4.5 V < V_{DDA_SD} < 5.5 V[8, 9] V_{RH_SD} = V_{DDA_SD} GAIN = 16	68	—	—	
$SNR_{DIFF333}$	Signal to noise ratio in differential mode, 333 Ksps output rate	4.5 V < V_{DDA_SD} < 5.5 V[8, 9] V_{RH_SD} = V_{DDA_SD} GAIN = 1	71	—	—	dB
		4.5 V < V_{DDA_SD} < 5.5 V[8, 9] V_{RH_SD} = V_{DDA_SD} GAIN = 2	70	—	—	
		4.5 V < V_{DDA_SD} < 5.5 V[8, 9] V_{RH_SD} = V_{DDA_SD} GAIN = 4	68	—	—	
		4.5 V < V_{DDA_SD} < 5.5 V[8, 9] V_{RH_SD} = V_{DDA_SD} GAIN = 8	65	—	—	
		4.5 V < V_{DDA_SD} < 5.5 V[8, 9] V_{RH_SD} = V_{DDA_SD} GAIN = 16	62	—	—	

Table continues on the next page...

Table 18. SDADC electrical specifications (continued)

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
$t_{SETTLING}$	Settling time after mux change	Analog inputs are muxed HPF = ON	—	—	$2*\delta_{GROUP}$ + $3*f_{ADCD\_S}$	—
		HPF = OFF	—	—	$2*\delta_{GROUP}$ + $2*f_{ADCD\_S}$	
$t_{ODRECOVERY}$	Overdrive recovery time	After input comes within range from saturation HPF = ON	—	—	$2*\delta_{GROUP}$ + f_{ADCD_S}	—
		HPF = OFF	—	—	$2*\delta_{GROUP}$	
C_{S_D}	SDADC sampling capacitance after sampling switch[16]	GAIN = 1, 2, 4, 8	—	—	75*GAIN	fF
		GAIN = 16	—	—	600	fF
I_{BIAS}	Bias consumption	At least one SDADC enabled	—	—	3.5	mA
I_{ADV_D}	SDADC supply consumption	Per SDADC enabled	—	—	4.325	mA
I_{ADR_D}	SDADC reference current consumption	Per SDADC enabled	—	—	20	µA

1. For input voltage above the maximum and below the clamp voltage of the input pad, there is no latch-up concern, and the signal will only be “clipped.”
2. VINP is the input voltage applied to the positive terminal of the SDADC
3. VINM is the input voltage applied to the negative terminal of the SDADC
4. Sampling is generated internally $f_{SAMPLING} = f_{ADCD\_M}/2$
5. For Gain = 16, SDADC resolution is 15 bit.
6. Calibration of gain is possible when gain = 1. Offset Calibration should be done with respect to $0.5*V_{RH\_SD}$ for differential mode and single ended mode with negative input = $0.5*V_{RH\_SD}$. Offset Calibration should be done with respect to 0 for single ended mode with negative input = 0. Both Offset and Gain Calibration is guaranteed for +/–5% variation of V_{RH_SD}, +/–10% variation of V_{DDA_SD}, +/–50 C temperature variation.
7. Offset and gain error due to temperature drift can occur in either direction (+/–) for each of the SDADCs on the device.
8. SDADC is functional in the range $3.6\ V < V_{DDA\_SD} < 4.0\ V$: SNR parameter degrades by 3 dB. SDADC is functional in the range $3.0\ V < V_{RH\_SD} < 4.0\ V$: SNR parameter degrades by 9 dB.
9. SNR values guaranteed only if external noise on the ADC input pin is attenuated by the required SNR value in the frequency range of $f_{ADCD\_M} - f_{ADCD\_S}$ to $f_{ADCD\_M} + f_{ADCD\_S}$, where f_{ADCD_M} is the input sampling frequency and f_{ADCD_S} is the output sample frequency. A proper external input filter should be used to remove any interfering signals in this frequency range.
10. Input impedance in differential mode $Z_{IN} = Z_{DIFF}$
11. Input impedance given at f_{ADCD_M} = 16 MHz. Impedance is inversely proportional to SDADC clock frequency. Z_{DIFF} (f_{ADCD_M}) = (16 MHz / f_{ADCD_M}) * Z_{DIFF}, Z_{CM} (f_{ADCD_M}) = (16 MHz / f_{ADCD_M}) * Z_{CM}.
12. Input impedance in single-ended mode $Z_{IN} = (2 * Z_{DIFF} * Z_{CM}) / (Z_{DIFF} + Z_{CM})$
13. V_{INTCM} is the Common Mode input reference voltage for the SDADC. It has a nominal value of $(V_{RH\_SD} - V_{RL\_SD}) / 2$.
14. The ±1% passband ripple specification is equivalent to $20 * \log_{10}(0.99) = 0.087$ dB.
15. Propagation of the information from the pin to the register CDR[CDATA] and the flags SFR[DFEF] and SFR[DFFF] is given by the different modules that must be crossed: delta/sigma filters, high pass filter, FIFO module, and clock domain synchronizers. The time elapsed between data availability at the pin and internal SDADC module registers is given by the following formula, where f_{ADCD_S} is the frequency of the sampling clock, f_{ADCD_M} is the frequency of the modulator, and $f_{FM\_PER\_CLK}$ is the frequency of the peripheral bridge clock feeds to the SDADC module:

    REGISTER LATENCY = $t_{LATENCY} + 0.5/f_{ADCD\_S} + 2\ (\sim+1)/f_{ADCD\_M} + 2(\sim+1)f_{FM\_PER\_CLK}$

    The (~+1) symbol refers to the number of clock cycles uncertainty (from 0 to 1 clock cycle) to be added due to resynchronization of the signal during clock domain crossing.

Table 26. Recommended operating characteristics

Part name	Part type	Nominal	Description
Q1	p-MOS	3 A - 20 V	SQ2301ES / FDC642P or equivalent: low threshold p-MOS, Vth < 2.0 V, Rdson @ 4.5 V < 100 mΩ, Cg < 5 nF
D1	Schottky	2 A - 20 V	SS8P3L or equivalent: Vishay™ low Vf Schottky diode
L	Inductor	3−4 µH - 1.5 A	Buck shielded coil low ESR
CI	Capacitor	22 µF - 20 V	Ceramic capacitor, total ESR < 70 mΩ
CE	Capacitor	0.1 µF - 7 V	Ceramic—one capacitor for each V_{DD} pin
CV	Capacitor	22 µF - 20 V	Ceramic V_{DDPMC} (optional 0.1 µF capacitor in parallel)
CD	Capacitor	22 µF - 20 V	Ceramic supply decoupling capacitor, ESR < 50 mΩ (as close as possible to the p-MOS source)
R	Resistor	2.0-4.7 kΩ	Pullup for power p-MOS gate
CB	Capacitor	22 µF - 20 V	Ceramic, connect 100 nF capacitor in parallel (as close as possible to package to reduce current loop from V_{DDPWR} to V_{SSPWR})

The following diagram shows the SMPS configuration connection.

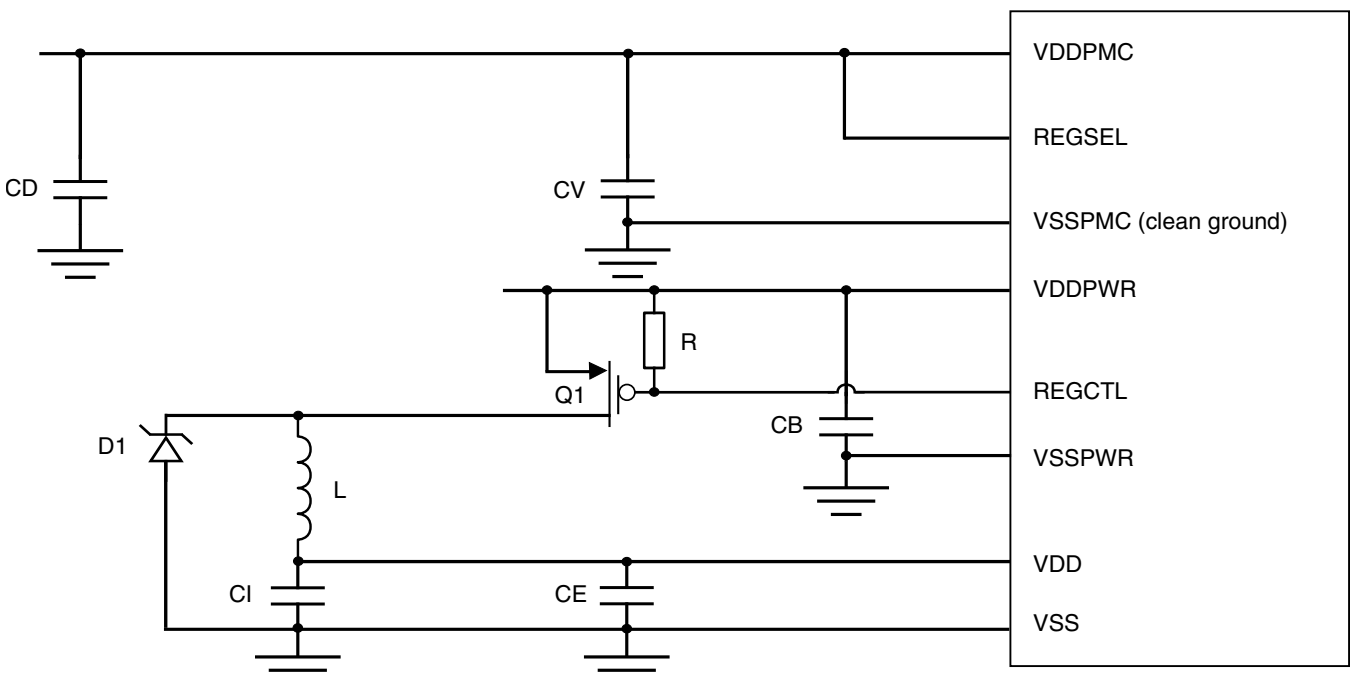

Figure 13. SMPS configuration

NOTE

The REGSEL pin is tied to V_{DDPMC} to select SMPS. If REGSEL is 0, the chip boots with the linear regulator.

See Power sequencing requirements for details about V_{DDPMC} and V_{DDPWR}.

3.12 Flash memory specifications

3.12.1 Flash memory program and erase specifications

NOTE

All timing, voltage, and current numbers specified in this section are defined for a single embedded flash memory within an SoC, and represent average currents for given supplies and operations.

Table 30 shows the estimated Program/Erase times.

Table 30. Flash memory program and erase specifications

Symbol	Characteristic[1]	Typ[2]	Factory Programming[3, 4]		Field Update			Unit
			Initial Max	Initial Max, Full Temp	Typical End of Life[5]	Lifetime Max[6]		
			20°C ≤T_A ≤30°C	-40°C ≤T_J ≤150°C	-40°C ≤T_J ≤150°C	≤ 1,000 cycles	≤ 250,000 cycles	
t_{dwpgm}	Doubleword (64 bits) program time	43	100	150	55	500		µs
t_{ppgm}	Page (256 bits) program time	73	200	300	108	500		µs
t_{qppgm}	Quad-page (1024 bits) program time	268	800	1,200	396	2,000		µs
t_{16kers}	16 KB Block erase time	168	290	320	250	1,000		ms
t_{16kpgm}	16 KB Block program time	34	45	50	40	1,000		ms
t_{32kers}	32 KB Block erase time	217	360	390	310	1,200		ms
t_{32kpgm}	32 KB Block program time	69	100	110	90	1,200		ms
t_{64kers}	64 KB Block erase time	315	490	590	420	1,600		ms
t_{64kpgm}	64 KB Block program time	138	180	210	170	1,600		ms
$t_{256kers}$	256 KB Block erase time	884	1,520	2,030	1,080	4,000	—	ms
$t_{256kpgm}$	256 KB Block program time	552	720	880	650	4,000	—	ms

1. Program times are actual hardware programming times and do not include software overhead. Block program times assume quad-page programming.
2. Typical program and erase times represent the median performance and assume nominal supply values and operation at 25 °C. Typical program and erase times may be used for throughput calculations.
3. Conditions: ≤ 150 cycles, nominal voltage.
4. Plant Programing times provide guidance for timeout limits used in the factory.
5. Typical End of Life program and erase times represent the median performance and assume nominal supply values. Typical End of Life program and erase values may be used for throughput calculations.
6. Conditions: -40°C ≤ T_J ≤ 150°C, full spec voltage.

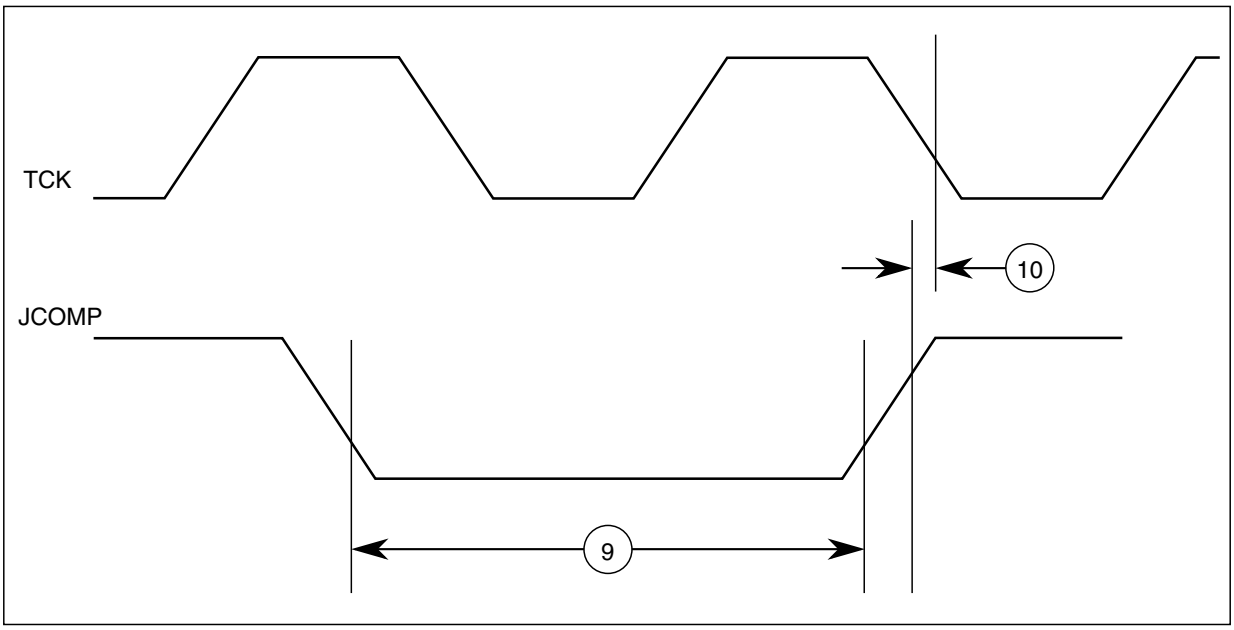

Figure 21. JTAG JCOMP timing

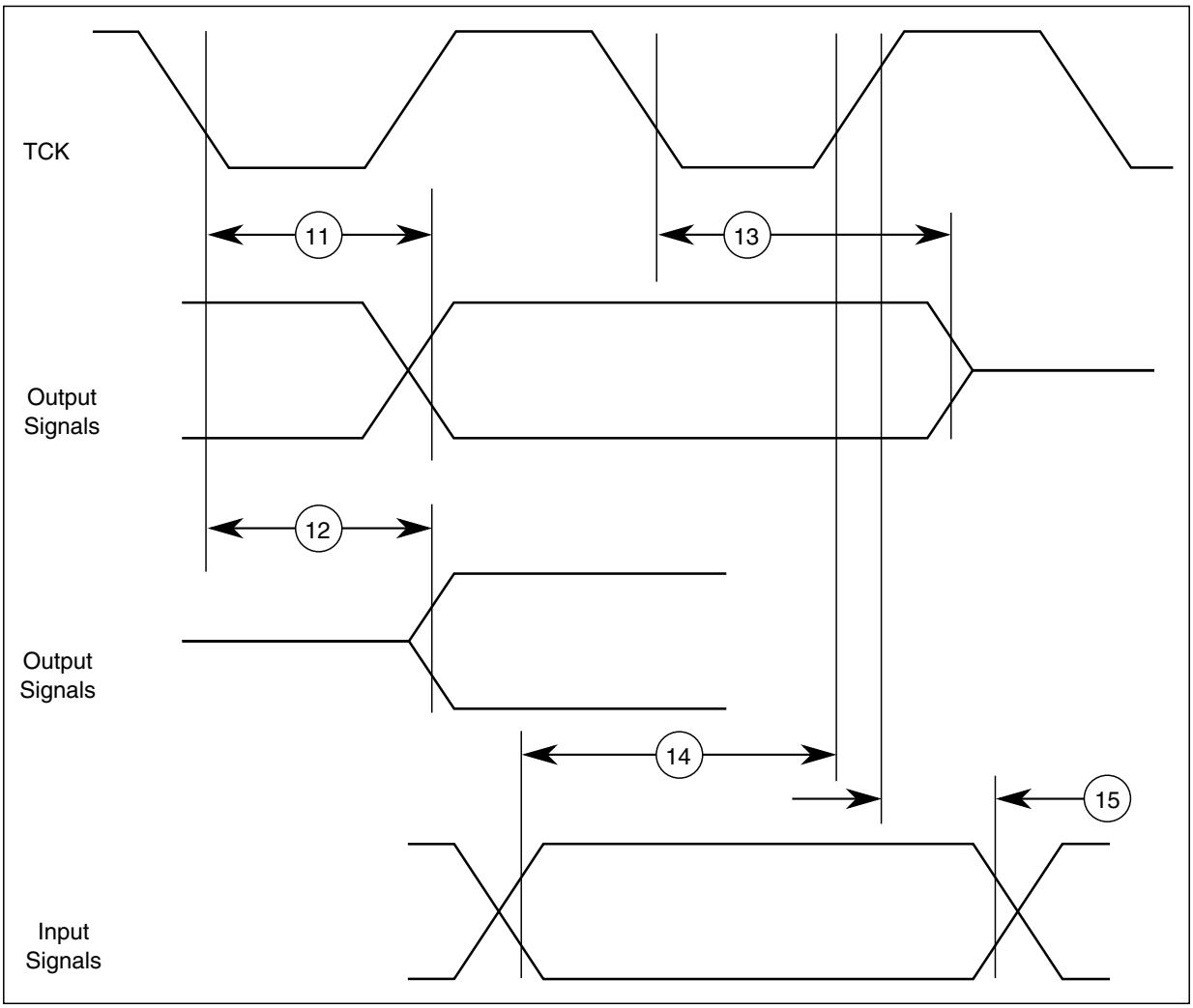

Figure 22. JTAG boundary scan timing

3.13.4 Nexus timing

Table 37. Nexus debug port timing[1]

Spec	Characteristic	Symbol	Min	Max	Unit
1	MCKO Cycle Time	t_{MCYC}	2	8	t_{CYC}
2	MCKO Duty Cycle	t_{MDC}	40	60	%
3	MCKO Low to MDO Data Valid[2]	t_{MDOV}	–0.1	0.2	t_{MCYC}
4	MCKO Low to $\overline{\text{MSEO}}$ Data Valid[2]	t_{MSEOV}	–0.1	0.2	t_{MCYC}
5	MCKO Low to $\overline{\text{EVTO}}$ Data Valid[2]	t_{EVTOV}	–0.1	0.2	t_{MCYC}
6	$\overline{\text{EVTI}}$ Pulse Width	t_{EVTIPW}	4.0	—	t_{TCYC}
7	$\overline{\text{EVTO}}$ Pulse Width	t_{EVTOPW}	1	—	t_{MCYC}
8	TCK Cycle Time	t_{TCYC}	2[3]	—	t_{CYC}

Table continues on the next page...

Table 37. Nexus debug port timing[1] (continued)

Spec	Characteristic	Symbol	Min	Max	Unit
8	Absolute minimum TCK cycle time[4] (TDO sampled on posedge of TCK)	t_{TCYC}	40[5]	—	ns
	Absolute minimum TCK cycle time[4] (TDO sampled on negedge of TCK)		20[5]	—	
9	TCK Duty Cycle	t_{TDC}	40	60	%
10	TDI, TMS Data Setup Time[6]	t_{NTDIS}, t_{NTMSS}	8	—	ns
11	TDI, TMS Data Hold Time[6]	T_{NTDIH}, t_{NTMSH}	5	—	ns
12	TCK Low to TDO Data Valid[6]	t_{NTDOV}	0	18	ns
13	$\overline{RDY}$ Valid to MCKO[7]	—	—	—	—
14	TDO hold time after TCLK low[6]	t_{NTDOH}	1	—	ns

1. All Nexus timing relative to MCKO is measured from 50% of MCKO and 50% of the respective signal. Nexus timing specified at V_{DD} = 1.08 V to 1.32 V, V_{DDE} = 3.0 V to 3.6 V, V_{DD33} and V_{DDSYN} = 3.0 V to 3.6 V, $T_A = T_L$ to T_H, and C_L = 30 pF with DSC = 0b10.
2. MDO, $\overline{MSEO}$, and $\overline{EVTO}$ data is held valid until next MCKO low cycle.
3. This is a functionally allowable feature. However, it may be limited by the maximum frequency specified by the absolute minimum TCK period specification.
4. This value is TDO propagation time plus 2 ns setup time to sampling edge.
5. This may require a maximum clock speed that is less than the maximum functional capability of the design depending on the actual system frequency being used.
6. Applies to TMS pin timing for the bit frame when using the 1149.7 advanced protocol.
7. The $\overline{RDY}$ pin timing is asynchronous to MCKO. The timing is guaranteed by design to function correctly.

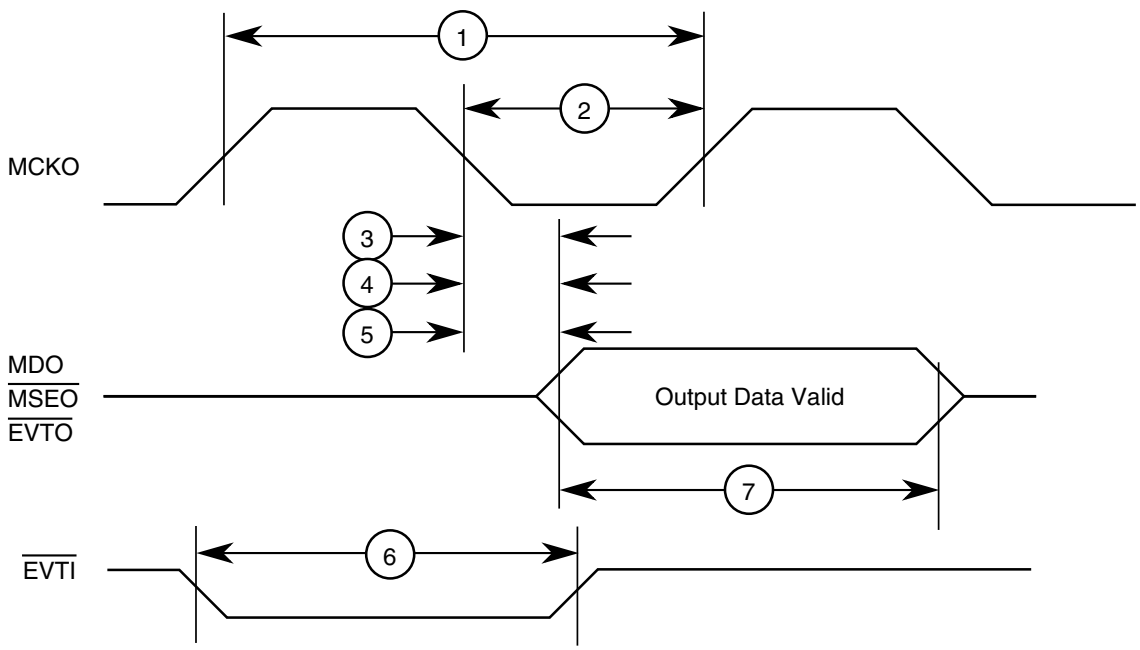

Figure 23. Nexus timings

Table 38. Bus operation timing[1] (continued)

Spec	Characteristic	Symbol	66 MHz (Ext. bus freq.)[2, 3]		Unit	Notes
			Min	Max		
10	D_ALE Negated to Address Invalid	t_{AAI}	2.0/1.0 [5]	—	ns	The timing is for Asynchronous external memory system. ALE is measured at 50% of VDDE.

1. EBI timing specified at V_{DD} = 1.08 V to 1.32 V, V_{DDE} = 3.0 V to 3.6 V, $T_A = T_L$ to T_H, and C_L = 30 pF with SIU_PCR[DSC] = 10b for ADDR/CTRL and SIU_PCR[DSC] = 11b for CLKOUT/DATA.
2. Speed is the nominal maximum frequency. Max speed is the maximum speed allowed including frequency modulation (FM).
3. Depending on the internal bus speed, set the SIU_ECCR[EBDF] bits correctly not to exceed maximum external bus frequency. The maximum external bus frequency is 66 MHz.
4. Refer to D_CLKOUT pad timing in Table 10.
5. ALE hold time spec is temperature dependant. 1.0 ns spec applies for temperature range -40 to 0°C. 2.0ns spec applies to temperatures > 0°C. This spec has no dependency on the SIU_ECCR[EBTS] bit.

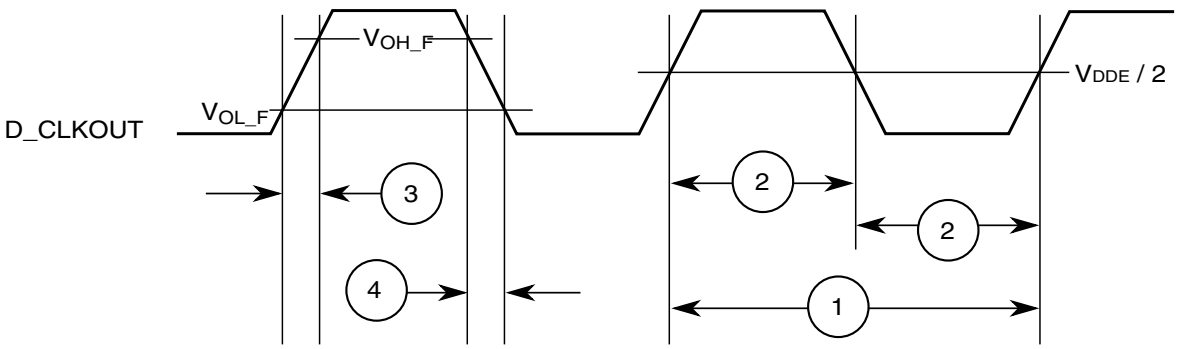

Figure 25. D_CLKOUT timing

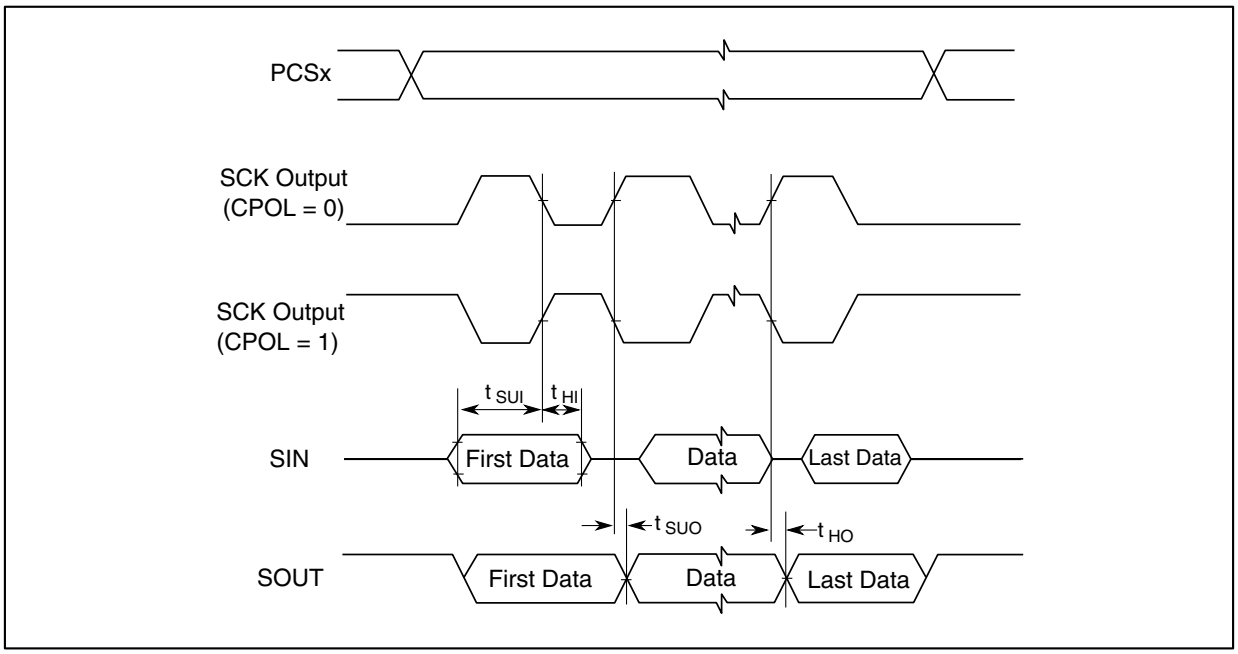

Figure 33. DSPI CMOS master mode – classic timing, CPHA = 1

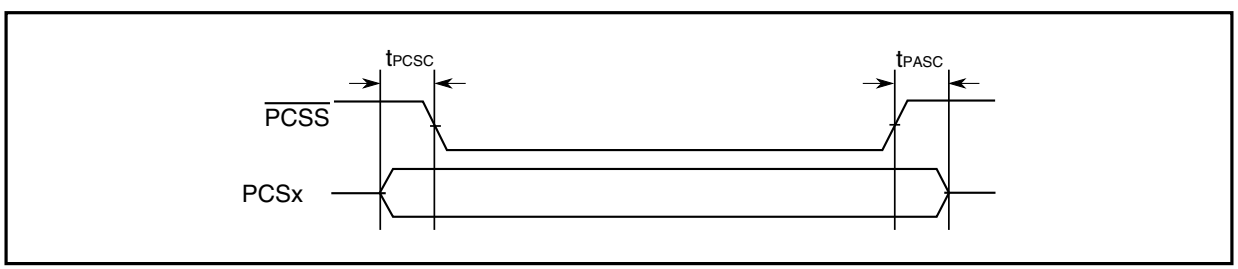

Figure 34. DSPI PCS strobe ($\overline{\text{PCSS}}$) timing (master mode)

3.13.9.1.2 DSPI CMOS Master Mode – Modified Timing

Table 44. DSPI CMOS master modified timing (full duplex and output only) – MTFE = 1, CPHA = 0 or 1[1]

#	Symbol	Characteristic	Condition[2]		Value[3]		Unit
			Pad drive[4]	Load (C_L)	Min	Max	
1	t_{SCK}	SCK cycle time	PCR[SRC]=11b	25 pF	33.0	—	ns
			PCR[SRC]=10b	50 pF	80.0	—	
			PCR[SRC]=01b	50 pF	200.0	—	
2	t_{CSC}	PCS to SCK delay	PCR[SRC]=11b	25 pF	($N^5 \times t_{SYS}$, [6]) – 16	—	ns
			PCR[SRC]=10b	50 pF	($N^5 \times t_{SYS}$, [6]) – 16	—	
			PCR[SRC]=01b	50 pF	($N^5 \times t_{SYS}$, [6]) – 18	—	
			PCS: PCR[SRC]=01b SCK: PCR[SRC]=10b	50 pF	($N^5 \times t_{SYS}$, [6]) – 45	—	

Table continues on the next page...

Table 44. DSPI CMOS master modified timing (full duplex and output only) – MTFE = 1, CPHA = 0 or 1[1] (continued)

#	Symbol	Characteristic	Condition[2]		Value[3]		Unit
			Pad drive[4]	Load (C_L)	Min	Max	
3	t_{ASC}	After SCK delay	PCR[SRC]=11b	PCS: 0 pF SCK: 50 pF	($M^7 \times t_{SYS}$, 6) – 35	—	ns
			PCR[SRC]=10b	PCS: 0 pF SCK: 50 pF	($M^7 \times t_{SYS}$, 6) – 35	—	
			PCR[SRC]=01b	PCS: 0 pF SCK: 50 pF	($M^7 \times t_{SYS}$, 6) – 35	—	
			PCS: PCR[SRC]=01b SCK: PCR[SRC]=10b	PCS: 0 pF SCK: 50 pF	($M^7 \times t_{SYS}$, 6) – 35	—	
4	t_{SDC}	SCK duty cycle[8]	PCR[SRC]=11b	0 pF	$1/2t_{SCK}$ – 2	$1/2t_{SCK}$ + 2	ns
			PCR[SRC]=10b	0 pF	$1/2t_{SCK}$ – 2	$1/2t_{SCK}$ + 2	
			PCR[SRC]=01b	0 pF	$1/2t_{SCK}$ – 5	$1/2t_{SCK}$ + 5	
PCS strobe timing							
5	t_{PCSC}	PCSx to $\overline{PCSS}$ time[9]	PCR[SRC]=10b	25 pF	13.0	—	ns
6	t_{PASC}	$\overline{PCSS}$ to PCSx time[9]	PCR[SRC]=10b	25 pF	13.0	—	ns
SIN setup time							
7	t_{SUI}	SIN setup time to SCK CPHA = 0[10]	PCR[SRC]=11b	25 pF	29 – ($P^{11} \times t_{SYS}$, 6)	—	ns
			PCR[SRC]=10b	50 pF	31 – ($P^{11} \times t_{SYS}$, 6)	—	
			PCR[SRC]=01b	50 pF	62 – ($P^{11} \times t_{SYS}$, 6)	—	
		SIN setup time to SCK CPHA = 1[10]	PCR[SRC]=11b	25 pF	29.0	—	ns
			PCR[SRC]=10b	50 pF	31.0	—	
			PCR[SRC]=01b	50 pF	62.0	—	
SIN hold time							
8	t_{HI}[12]	SIN hold time from SCK CPHA = 0[10]	PCR[SRC]=11b	0 pF	–1 + ($P^{11} \times t_{SYS}$, 6)	—	ns
			PCR[SRC]=10b	0 pF	–1 + ($P^{11} \times t_{SYS}$, 6)	—	
			PCR[SRC]=01b	0 pF	–1 + ($P^{11} \times t_{SYS}$, 6)	—	
		SIN hold time from SCK CPHA = 1[10]	PCR[SRC]=11b	0 pF	–1.0	—	ns
			PCR[SRC]=10b	0 pF	–1.0	—	
			PCR[SRC]=01b	0 pF	–1.0	—	
SOUT data valid time (after SCK edge)							
9	t_{SUO}	SOUT data valid time from SCK CPHA = 0[13]	PCR[SRC]=11b	25 pF	—	7.0 + t_{SYS}[6]	ns
			PCR[SRC]=10b	50 pF	—	8.0 + t_{SYS}[6]	
			PCR[SRC]=01b	50 pF	—	18.0 + t_{SYS}[6]	
		SOUT data valid time from SCK CPHA = 1[13]	PCR[SRC]=11b	25 pF	—	7.0	ns
			PCR[SRC]=10b	50 pF	—	8.0	
			PCR[SRC]=01b	50 pF	—	18.0	
SOUT data hold time (after SCK edge)							

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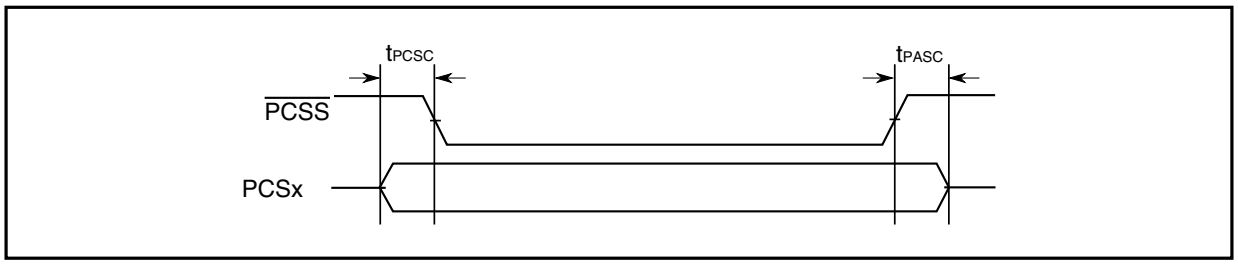


Figure 37. DSPI PCS strobe ($\overline{\text{PCSS}}$) timing (master mode)

3.13.9.1.3 DSPI LVDS Master Mode – Modified Timing

Table 45. DSPI LVDS master timing – full duplex – modified transfer format (MTFE = 1), CPHA = 0 or 1

#	Symbol	Characteristic	Condition[1]		Value[2]		Unit
			Pad drive[3]	Load (C_L)	Min	Max	
1	t_{SCK}	SCK cycle time	LVDS	15 pF to 25 pF differential	33.3	—	ns
2	t_{CSC}	PCS to SCK delay (LVDS SCK)	PCS: PCR[SRC]=11b	25 pF	($N^4 \times t_{SYS}$, [5]) – 10	—	ns
			PCS: PCR[SRC]=10b	50 pF	($N^4 \times t_{SYS}$, [5]) – 10	—	ns
			PCS: PCR[SRC]=01b	50 pF	($N^4 \times t_{SYS}$, [5]) – 32	—	ns
3	t_{ASC}	After SCK delay (LVDS SCK)	PCS: PCR[SRC]=11b	PCS: 0 pF SCK: 25 pF	($M^6 \times t_{SYS}$, [5]) – 8	—	ns
			PCS: PCR[SRC]=10b	PCS: 0 pF SCK: 25 pF	($M^6 \times t_{SYS}$, [5]) – 8	—	ns
			PCS: PCR[SRC]=01b	PCS: 0 pF SCK: 25 pF	($M^6 \times t_{SYS}$, [5]) – 8	—	ns
4	t_{SDC}	SCK duty cycle[7]	LVDS	15 pF to 25 pF differential	$1/2t_{SCK}$ – 2	$1/2t_{SCK}$ +2	ns
7	t_{SUI}	**SIN setup time**					
		SIN setup time to SCK CPHA = 0[8]	LVDS	15 pF to 25 pF differential	23 – ($P^9 \times t_{SYS}$, [5])	—	ns
		SIN setup time to SCK CPHA = 1[8]	LVDS	15 pF to 25 pF differential	23	—	ns
8	t_{HI}	**SIN hold time**					
		SIN hold time from SCK CPHA = 0[8]	LVDS	0 pF differential	–1 + ($P^9 \times t_{SYS}$, [5])	—	ns
		SIN hold time from SCK CPHA = 1[8]	LVDS	0 pF differential	–1	—	ns

Table continues on the next page...

Table 45. DSPI LVDS master timing – full duplex – modified transfer format (MTFE = 1), CPHA = 0 or 1 (continued)

#	Symbol	Characteristic	Condition[1]		Value[2]		Unit
			Pad drive[3]	Load (C_L)	Min	Max	
9	t_{SUO}	**SOUT data valid time (after SCK edge)**					
		SOUT data valid time from SCK CPHA = 0[10]	LVDS	15 pF to 25 pF differential	—	7.0 + t_{SYS}[5]	ns
		SOUT data valid time from SCK CPHA = 1[10]	LVDS	15 pF to 25 pF differential	—	7.0	ns
10	t_{HO}	**SOUT data hold time (after SCK edge)**					
		SOUT data hold time after SCK CPHA = 0[10]	LVDS	15 pF to 25 pF differential	–7.5 + t_{SYS}[5]	—	ns
		SOUT data hold time after SCK CPHA = 1[10]	LVDS	15 pF to 25 pF differential	–7.5	—	ns

1. When a characteristic involves two signals, the pad drive and load conditions apply to each signal's pad, unless specified otherwise.
2. All timing values for output signals in this table are measured to 50% of the output voltage.
3. Pad drive is defined as the PCR[SRC] field setting in the SIU. Timing is guaranteed to same drive capabilities for all signals; mixing of pad drives may reduce operating speeds and may cause incorrect operation.
4. N is the number of clock cycles added to time between PCS assertion and SCK assertion and is software programmable using DSPI_CTARx[PSSCK] and DSPI_CTARx[CSSCK]. The minimum value is 2 cycles unless TSB mode or Continuous SCK clock mode is selected, in which case, N is automatically set to 0 clock cycles (PCS and SCK are driven by the same edge of DSPI_CLKn).
5. t_{SYS} is the period of DSPI_CLKn clock, the input clock to the DSPI module. Maximum frequency is 100 MHz (min tSYS = 10 ns).
6. M is the number of clock cycles added to time between SCK negation and PCS negation and is software programmable using DSPI_CTARx[PASC] and DSPI_CTARx[ASC]. The minimum value is 2 cycles unless TSB mode or Continuous SCK clock mode is selected, in which case, M is automatically set to 0 clock cycles (PCS and SCK are driven by the same edge of DSPI_CLKn).
7. t_{SDC} is only valid for even divide ratios. For odd divide ratios the fundamental duty cycle is not 50:50. For these odd divide ratios cases, the absolute spec number is applied as jitter/uncertainty to the nominal high time and low time.
8. Input timing assumes an input slew rate of 1 ns (10% – 90%) and LVDS differential voltage = ±100 mV.
9. P is the number of clock cycles added to delay the DSPI input sample point and is software programmable using DSPI_MCR[SMPL_PT]. The value must be 0, 1 or 2. If the baud rate divide ratio is /2 or /3, this value is automatically set to 1.
10. SOUT Data Valid and Data hold are independent of load capacitance if SCK and SOUT load capacitances are the same value.

1 mm of wire extending from the junction. Place the thermocouple wire flat against the package case to avoid measurement errors caused by the cooling effects of the thermocouple wire.

When board temperature is perfectly defined below the device, it is possible to use the thermal characterization parameter (Ψ_{JPB}) to determine the junction temperature by measuring the temperature at the bottom center of the package case (exposed pad) using the following equation:

$$T_J = T_B + (\Psi_{JPB} x P_D)$$

where:

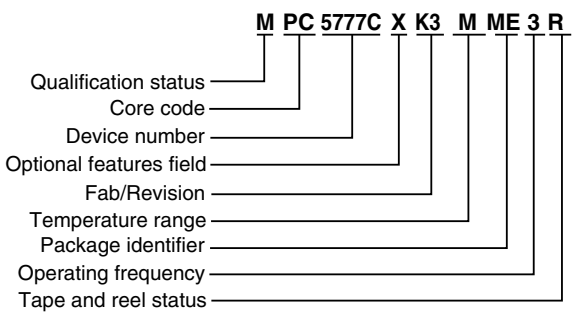
T_T = thermocouple temperature on bottom of the package (°C)

Ψ_{JT} = thermal characterization parameter (°C/W)

P_D = power dissipation in the package (W)

5 Ordering information

Figure 47 and Table 56 describe orderable part numbers for the MPC5777C.



Temperature range
M = –40 °C to 125 °C

Operating frequency
3 = 2 x 264 MHz

Package identifier
ME = 416 MAPBGA Pb-Free
MO = 516 MAPBGA Pb-Free

Tape and reel status
R = Tape and reel
(blank) = Trays

Qualification status
P = Pre-qualification
M = Fully spec. qualified, general market flow
S = Fully spec. qualified, automotive flow

Optional features field
(blank) = ISO-compliant CAN FD not available, trimmed for SMPS or external regulator, and includes SHE-compliant security firmware version 2.07
A = ISO-compliant CAN FD not available, trimmed for SMPS or external regulator, and includes SHE-compliant security firmware version 2.08
R = ISO-compliant CAN FD not available, trimmed for LDO regulator, and includes SHE-compliant security firmware version 2.08
C = ISO-compliant CAN FD available, trimmed for SMPS or external regulator, and includes SHE-compliant security firmware version 2.07
D = ISO-compliant CAN FD available, trimmed for SMPS or external regulator, and includes SHE-compliant security firmware version 2.08
L = ISO-compliant CAN FD available, trimmed for LDO regulator, and includes SHE-compliant security firmware version 2.08
S = ISO-compliant CAN FD available, trimmed for SMPS or external regulator, and includes RSA-enhanced security firmware
T = ISO-compliant CAN FD available, trimmed for LDO regulator, and includes RSA-enhanced security firmware

Note: Not all options are available on all devices.

Figure 47. MPC5777C Orderable part number description

Table 56. Example orderable part numbers

Part number[1]	Package description	Speed (MHz)[2]	Operating temperature[3]	
			Min (T_L)	Max (T_H)
SPC5777CCK3MME3	MPC5777C 416 package Lead-free (Pb-free)	264	–40 °C	125 °C
SPC5777CK3MME3	MPC5777C 416 package Lead-free (Pb-free)	264	–40 °C	125 °C
SPC5777CCK3MMO3	MPC5777C 516 package Lead-free (Pb-free)	264	–40 °C	125 °C
SPC5777CK3MMO3	MPC5777C 516 package Lead-free (Pb-free)	264	–40 °C	125 °C

1. All packaged devices are PPC5777C, rather than MPC5777C or SPC5777C, until product qualifications are complete. The unpackaged device prefix is PCC, rather than SCC, until product qualification is complete.

   Not all configurations are available in the PPC parts.
2. For the operating mode frequency of various blocks on the device, see Table 3.
3. The lowest ambient operating temperature is referenced by T_L; the highest ambient operating temperature is referenced by T_H.

6 Document revision history

The following table summarizes revisions to this document since the previous release.

Table 57. Revision history

Revision	Date	Description of changes
11	04/2017	In Figure 47 of Ordering information, added codes and firmware version information in definition of "Optional features field" • At end of line for *(blank)*, added "version 2.07" • Added line for *A* • At end of line for *R*, added "version 2.08" • At end of line for *C*, added "version 2.07" • Added line for *D* • At end of line for *L*, added "version 2.08"

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Document Number MPC5777C
Revision 11, 04/2017